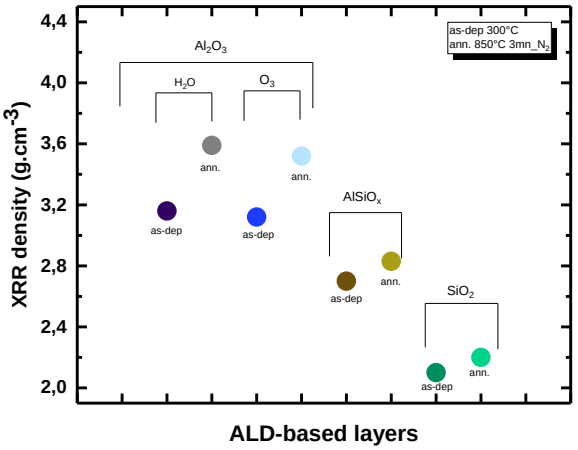

Figure 1: XRR density of ALD-$AlSiO_x$ layers vs Al_2O_3 and SiO_2 layers (as-deposited and after annealing@850°C, 3mn)

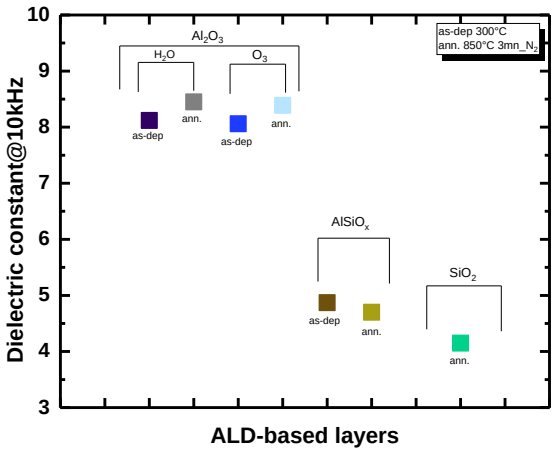

Figure 2: Dielectric constant of ALD-$AlSiO_x$ layers vs Al_2O_3 and SiO_2 layers (as-deposited and after annealing@850°C, 3mn)

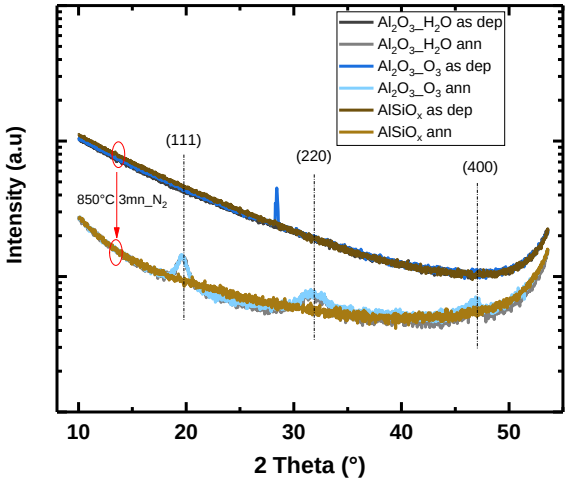

Figure 3: GIXRD structures of ALD-$AlSiO_x$ layers vs Al_2O_3 layers (as-deposited using H_2O or O_3 oxidant and after annealing@850°C, 3mn)

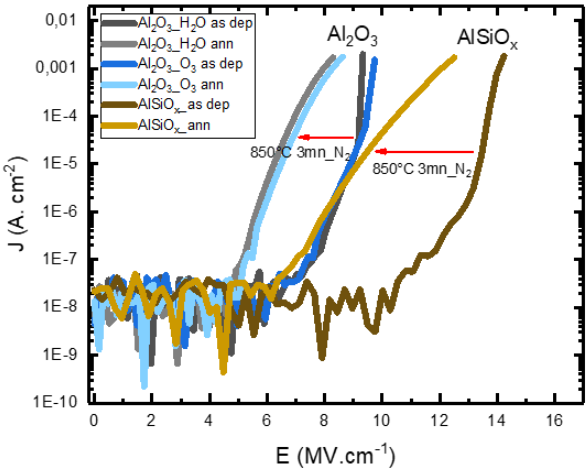

Figure 4: Leakage current of ALD-$AlSiO_x$ layers vs Al_2O_3 (as-deposited using H_2O or O_3 oxidant and after annealing@850°C, 3mn)